

Strong Valence Fluctuation Effects in $\text{Sm}Tr_2\text{Al}_{20}$ ($Tr = \text{Ti, V, Cr}$)

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We present a single crystal study of low temperature magnetism and transport in $\text{Sm}Tr_2\text{Al}_{20}$ ($Tr = \text{Ti, V}$ and Cr). Strong valence fluctuation is manifested as Kondo effects including a large Sommerfeld coefficient γ , a weak temperature dependence of magnetic susceptibility and a $-\ln T$ dependent resistivity. All the systems order antiferromagnetically at $T_N = 6.4$ K (Ti), 2.9 K (V) and 1.8 K (Cr). A systematic change in the susceptibility, specific heat, and resistivity indicates that stronger c - f hybridization in $\text{SmV}_2\text{Al}_{20}$ and $\text{SmCr}_2\text{Al}_{20}$ than in $\text{SmTi}_2\text{Al}_{20}$ suppresses T_N and induces the valence fluctuations, and moreover, field-insensitive heavy fermion states.

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Sm-based intermetallics have attracted much attention in the research of strongly correlated f -electron systems for their rich variety of physical phenomena. One significant characteristic property of the Sm ion is the valence degree of freedom. For instance, $\text{Sm}X$ ($X=\text{Te, Se, S}$) exhibits a semiconductor-metal transition under pressure, showing a jump in valence^{1,2}. SmB_6 is known as a canonical Kondo insulator with intermediate valence³. Although quite rare in Sm-based systems, the Kondo effect is observed in SmSn_3 and $\text{SmFe}_4\text{P}_{12}$ as $-\ln T$ dependence of the resistivity^{4,5}. Recent extensive work on filled skutterudite compounds^{6,7} has elucidated that when located at a highly symmetric center of a cage, the Sm ion may induce interesting physical properties. $\text{SmRu}_4\text{P}_{12}$ shows a metal-insulator transition at $T_{\text{MI}} = 16.5$ K and an octupole order below T_{MI} has been proposed to explain the sharp drop in the elastic constant^{8,9}. Unusual field-insensitive heavy-fermion behavior has been discovered in $\text{SmOs}_4\text{Sb}_{12}$ ^{10,11}. Several candidates of the mechanism are proposed, such as mixed valence¹²⁻¹⁵ and anharmonic oscillation in a cage called the rattling vibration¹⁶⁻¹⁹.

The $\text{CeCr}_2\text{Al}_{20}$ -type compounds $R\text{Tr}_2\text{Al}_{20}$ (R : rare earth; Tr : transition metal) provide another cage structure similar to the filled skutterudite compounds. They have a space group $Fd\bar{3}m$ and the symmetry of the R site is T_d and cubic. The number of Al constructing the cage is 16, in comparison with 12 for the filled skutterudites and is the largest for the coordination number of tetrahedral groupings of spheres²⁰. It suggests that the number of channels of Kondo coupling should be large in this system, and in fact, our recent study on the $\text{PrTr}_2\text{Al}_{20}$ systems reveals strong hybridization effects between $\text{Pr-}4f$ electrons and conduction(c) electrons²¹. Therefore, the Sm analogs may exhibit strong c - f hybridization effects and thus show interesting phenomena.

In this Rapid Communication, we report the results of single-crystal studies on the low-temperature magnetism and transport of $\text{SmTr}_2\text{Al}_{20}$ ($Tr = \text{Ti, V, Cr}$). Antiferromagnetic orders are observed at $T_N = 6.4$ K (Ti), 2.9 K (V) and 1.8 K (Cr). The entropy of these compounds saturates to $R \ln 4$, showing that the magnetic order is based on the Γ_8 quartet of the $J = 5/2$ multiplet. Interestingly, the enhancement of the Sommerfeld coefficient γ is observed as T_N is suppressed by substitution, which reaches 1000 (mJ/mol K²) for $\text{SmCr}_2\text{Al}_{20}$. Magnetic susceptibilities exhibit nearly temperature independent behavior, indicating strong valence fluctuation. The systematic change in the susceptibility and the $-\ln T$ dependence of the resistivity reveals that the c - f hybridization becomes enhanced in the sequence from $Tr = \text{Ti, V, to Cr}$, inducing the Kondo effect, which has been rarely seen in Sm-based Kondo lattice systems. Moreover, our specific heat measurements found that the low-temperature heavy fermion state is significantly insensitive to magnetic field at least up to 9 T, suggesting a role of the nonmagnetic Sm^{2+} state stabilized by the valence fluctuation.

Single crystals of $\text{SmTr}_2\text{Al}_{20}$ ($Tr = \text{Ti, V, Cr}$) were grown by the Al self-flux method under vacuum, using $4N(99.99\%)$ -Sm, $3N$ - Tr and $5N$ -Al. The starting ratio of the elements was 1 : 2 : 45. They were prepared in alumina crucibles and sealed in silica tubes and slowly cooled from 1150 to 750 °C for 60 h. The crystal structure was verified to be of cubic $\text{CeCr}_2\text{Al}_{20}$ type with the space group $Fd\bar{3}m$ by the x-ray powder and single-crystal diffraction measurements and is found to have lattice parameters $a = 14.723$ Å (Ti), 14.571 Å (V), 14.501 Å (Cr), all of which are consistent with the previous report²². The electrical resistivity ρ and specific heat C_P above 0.4 K were measured by the standard four-probe dc method and a thermal relaxation method, respectively. The dc magnetic susceptibility χ above 2 K was measured by a commercial superconducting quantum interference device (SQUID) magnetometer.

Figure 1(a) shows the $4f$ electron contribution to the specific heat C_{4f} under fields of 0 T (solid symbols) and 9 T (open symbols). This was estimated by subtracting C_P of the La analogs, namely $\text{LaTr}_2\text{Al}_{20}$ ²¹, from C_P of $\text{SmTr}_2\text{Al}_{20}$ ($Tr = \text{Ti, V, Cr}$). A sharp lambda-like anomaly of C_{4f} is observed at $T_N = 6.4$ K for $\text{SmTi}_2\text{Al}_{20}$, $T_N = 2.9$ K for $\text{SmV}_2\text{Al}_{20}$ and $T_N = 1.8$ K for $\text{SmCr}_2\text{Al}_{20}$, indicating a second-order phase transition. The temperature dependence of the entropy S_{4f} estimated by integrating C_{4f}/T vs. T is shown in Fig.1 (b). $S_{4f}(0.4$ K) and the Sommerfeld coefficient γ at $T = 0$ were estimated assuming a linear decrease of C_{4f}/T between T_N and $T = 0$ for $\text{SmV}_2\text{Al}_{20}$ and $\text{SmCr}_2\text{Al}_{20}$ (Fig. 1(b) broken lines). As for $\text{SmTi}_2\text{Al}_{20}$, the upturn of C/T below 1 K is ascribable a nuclear Schottky component, and we used the fitting form $C/T = \gamma + A/T^3$ (Fig. 1(b) inset, solid line). $S_{4f}(T)$ for all systems shows a saturation to $\sim R \ln 4$ at $T \sim 20$ K, indicating the ground quartet (Fig. 1(b)). If we assume that the $4f$ electrons of Sm^{3+} are localized, $J = 5/2$ multiplet splits into the doublet Γ_7 and the quartet Γ_8 because of the T_d cubic symmetry at the Sm site. Thus, the crystalline electric field (CEF) ground state should be the Γ_8 quartet and the gap Δ between the two CEF states should be larger than 40 K. The large Sommerfeld coefficient γ of ~ 100 (mJ/mol K²) for $\text{SmTi}_2\text{Al}_{20}$, ~ 720 (mJ/mol K²) for $\text{SmV}_2\text{Al}_{20}$ and ~ 1000 (mJ/mol K²) for $\text{SmCr}_2\text{Al}_{20}$ below T_N suggests that the electron mass is enhanced by a many-body correlation effect. In this type of Kondo lattice systems, the origin of the mass enhancement must be the c - f hybridization, and thus the increase in γ points to the corresponding increase in the hybridization strength and the approach toward a quantum critical point from a magnetic ordered side. Surprisingly, the shape of the specific heat including the large Sommerfeld coefficient γ does not change even under a field of 9 T (Fig1. (a)). It indicates that the ordered phase is insensitive to the magnetic field. A similar field insensitivity is sometimes observed in Sm compounds such as SmSn_3 , $\text{SmOs}_4\text{P}_{12}$ and $\text{SmPt}_4\text{Ge}_{12}$ ^{4,23,24}.

Figure 2 shows the temperature dependence of the $4f$ electron contribution to the magnetic susceptibility χ_{4f} . Here, χ_{4f} is estimated as the difference between M/H of $\text{SmTr}_2\text{Al}_{20}$ and $\text{LaTr}_2\text{Al}_{20}$ and is found isotropic under

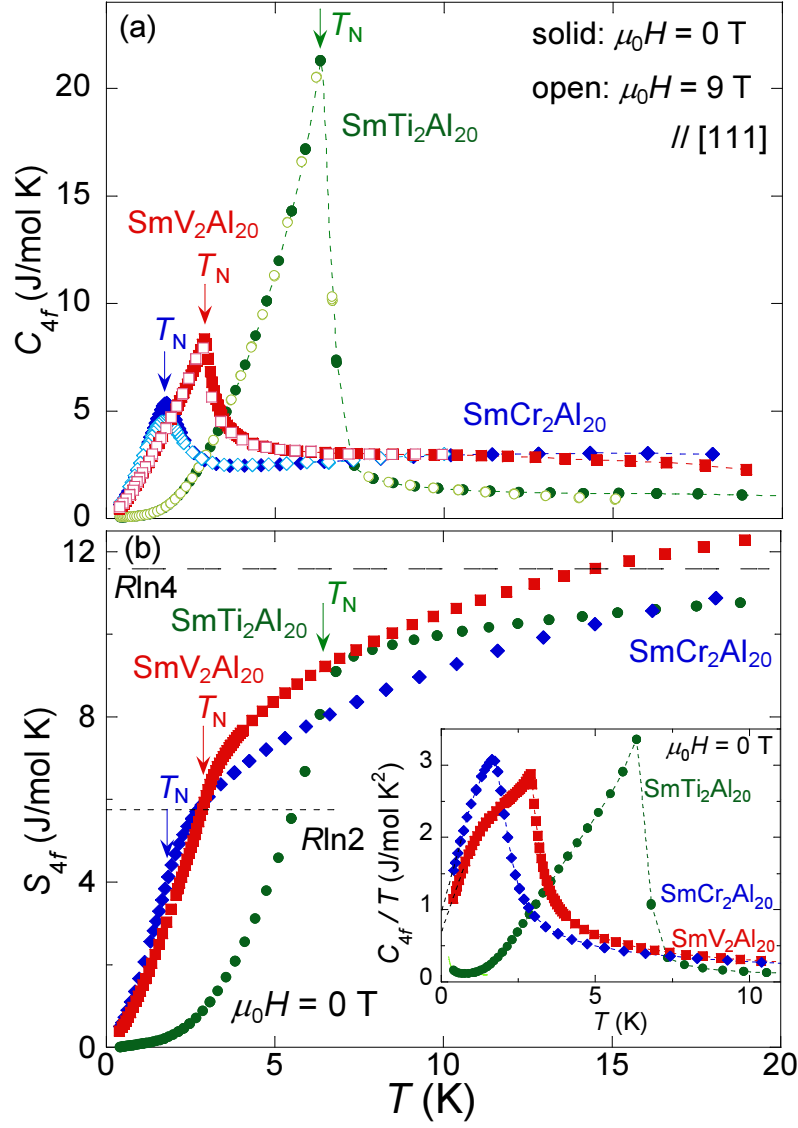


FIG. 1. (Color online) (a) Temperature dependence of the 4f contribution to the specific heat, C_{4f} , for SmTi₂Al₂₀ (circle), SmV₂Al₂₀ (square) and SmCr₂Al₂₀ (diamond) under $\mu_0 H = 0$ T (solid symbols) and 9 T (open symbols). Arrows indicate the transition temperatures defined as the peak temperature of $C_P(T)$. (b) Temperature dependence of the 4f electron contribution S_{4f} to the entropy. The horizontal dashed lines indicate $S_{4f} = R \ln 2$ and $R \ln 4$, respectively. Inset: T dependence of C_{4f}/T . To estimate the Sommerfeld coefficient γ at $T = 0$ and S_{4f} at 0.4 K, a linear extrapolation (dashed straight line) of C_{4f}/T to $T = 0$ is used. The solid line indicates the fitting to the form $C/T = \gamma + A/T^3$ for SmTi₂Al₂₀.

$\mu_0 H \leq 0.5$ T and above T_N . $\chi(T)$ of LaTr₂Al₂₀ is found nearly T -independent and Pauli paramagnetic (Fig 2 inset). Solid and dotted lines show $\chi^{3+}(T)$ and $\chi^{2+}(T)$ calculated for Sm³⁺ $4f^5$ $J = 5/2$ and Sm²⁺ $4f^6$ $J = 0$ single ion ground states, respectively. Here, we adopt a typical value of the spin orbit interaction $\lambda/k_B = 580$ K (Sm³⁺), 420 K (Sm²⁺)²⁵, CEF parameters $A_4\langle r^4 \rangle/k_B = -500$ K and $A_6\langle r^6 \rangle/k_B = 150$ K, leading to the CEF gap of ~ 200 K between Γ_8 and Γ_7 ²⁶.

Clearly, χ_{4f} of SmTr₂Al₂₀ shows a weaker temperature dependence than the calculation for the $\chi^{3+}(T)$. Only the upturn below ~ 20 K may come from the $J = 5/2$ multiplet. On the other hand, the temperature independent susceptibility at $50 \text{ K} < T < 150 \text{ K}$ for SmV₂Al₂₀ is ascribable to the Van Vleck susceptibility due to the off-diagonal term between $J = 0$ ground state and $J = 1$ excited state of Sm²⁺ ion. In addition, χ_{4f} of the V and Cr compounds at 350 K is larger than the results of Sm³⁺ CEF calculation. It indicates the existence of Sm²⁺ component, often observed in valence fluctuating Sm compounds such as SmS under pressure and SmB₆^{27,28}. By using the susceptibility at 350 K, we roughly estimate the ratio between Sm³⁺ and Sm²⁺ to be 0.8 : 0.2 for SmV₂Al₂₀ and 0.7 : 0.3 for

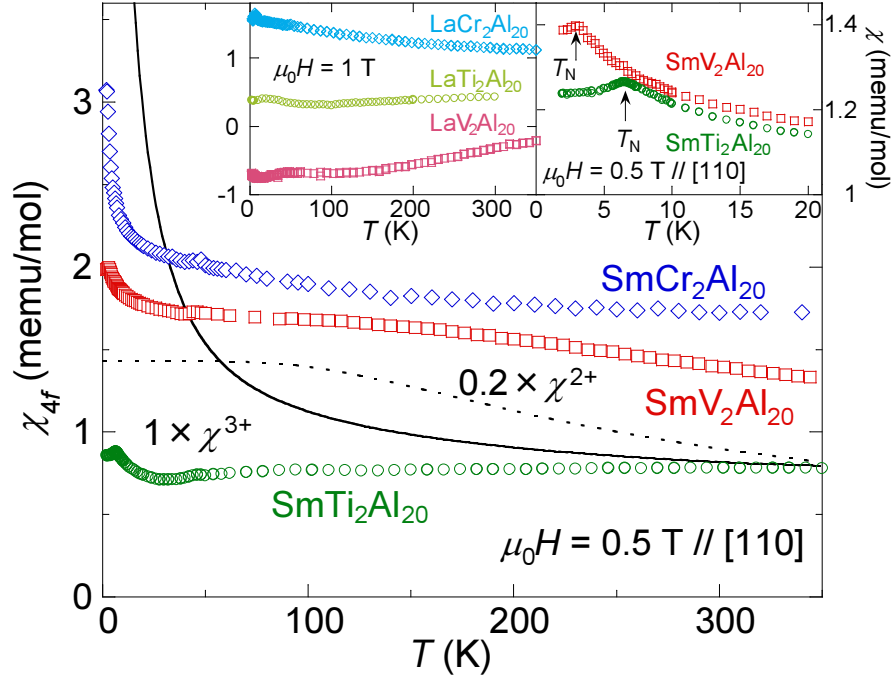


FIG. 2. (Color online) Temperature dependence of the magnetic susceptibility of the 4f electron contribution χ_{4f} for SmTi₂Al₂₀ (circle), SmV₂Al₂₀ (square) and SmCr₂Al₂₀ (diamond), and under $\mu_0 H = 0.5$ T // [110]. No anisotropy is found under the field below 0.5 T. The solid and dotted lines show $\chi^{3+}(T)$ and $\chi^{2+}(T)$ calculated for 4f⁵ $J = 5/2$ and 4f⁶ $J = 0$ single ion ground states, respectively. Left-hand inset: $\chi(T)$ of LaTr₂Al₂₀. Right-hand inset: Low temperature part of χ for SmTi₂Al₂₀ and SmV₂Al₂₀. The arrows indicate the transition temperatures defined as the cusp temperatures in $\chi(T)$.

SmCr₂Al₂₀. However, the experimental data of χ_{4f} is not fully reproduced by the sum of divalent and trivalent component of Sm ion, namely, $w\chi^{3+}(T) + (1-w)\chi^{2+}(T)$ below 200 K with the weight w for the Sm³⁺ component. This temperature scale is too high for antiferromagnetic fluctuations to be effective in this three dimensional material with low T_N . Instead, it indicates that the ratio between Sm³⁺ and Sm²⁺ is possibly temperature dependent and the valence decreases on cooling as found in SmOs₄Sb₁₂^{12,13}. Notably, the fact that the value of χ_{4f} at high temperatures is enhanced by substitution, corresponding to the increase in the Sm²⁺ component, indicates the valence fluctuations increase in order from SmTi₂Al₂₀, SmV₂Al₂₀, to SmCr₂Al₂₀.

The inset to Fig. 2 shows the low temperature part of the magnetic susceptibility χ for SmTi₂Al₂₀ and SmV₂Al₂₀ near T_N . The arrows show the transition temperature defined at the cusp of χ , which is almost consistent with the peak in the specific heat (Fig. 1(a)). T_N for SmCr₂Al₂₀ is lower than 2 K, the lowest T of the measurement. The decrease of χ below T_N indicates that the phase transitions seen in SmTi₂Al₂₀ and SmV₂Al₂₀ are antiferromagnetic transitions. The muon spin relaxation measurements have been carried out for SmTi₂Al₂₀ and SmCr₂Al₂₀, and showed the development of the internal field below T_N ²⁹, consistent with the antiferromagnetism.

Figure 3 shows the temperature dependence of the electrical resistivity $\rho(T)$ of the SmTr₂Al₂₀ systems. All Sm compounds exhibit a resistivity drop due to the magnetic order at T_N . T_N defined as the peak temperature of the specific heat are indicated by arrows and are consistent with the cusp in $\rho(T)$. Interestingly, $\rho(T)$ shows a $-\ln T$ dependence at $T_N < T < 30 \sim 40$ K. This is reminiscent of the Kondo effects seen in Ce, Yb, and U-based heavy-fermion compounds³¹. The CEF scheme alone cannot produce the $-\ln T$ dependence but only the T independent ρ in the T regime between T_N and the CEF gap Δ , which should be higher than 40 K for the current systems. In addition, since the $\rho(T)$ of LaTr₂Al₂₀ exhibits almost no temperature dependence in this T region, a phonon mechanism can be ruled out (Fig. 3). Note that the critical effects associated with the phase transition cannot be the origin of the increase of $\rho(T)$ starting below $T \sim 40$ K $\gg T_N$. Thus, it may well come from the Kondo effect based on the hybridization between conduction electrons and the magnetic Γ_8 state. In Sm compounds, such a Kondo effect has been rarely found, so far only in SmSn₃⁴ and SmFe₄P₁₂⁵, to the best of our knowledge.

The T - H phase diagram of the SmTr₂Al₂₀ systems constructed by measurements under fields along [100], [110] and [111] is shown in Fig. 4. For all compounds, no field direction dependence is seen, indicating the isotropic nature of the phase boundaries. The transition temperature $T_N(H)$ is determined as the peak T of $C_P(T)$ (solid symbols) and

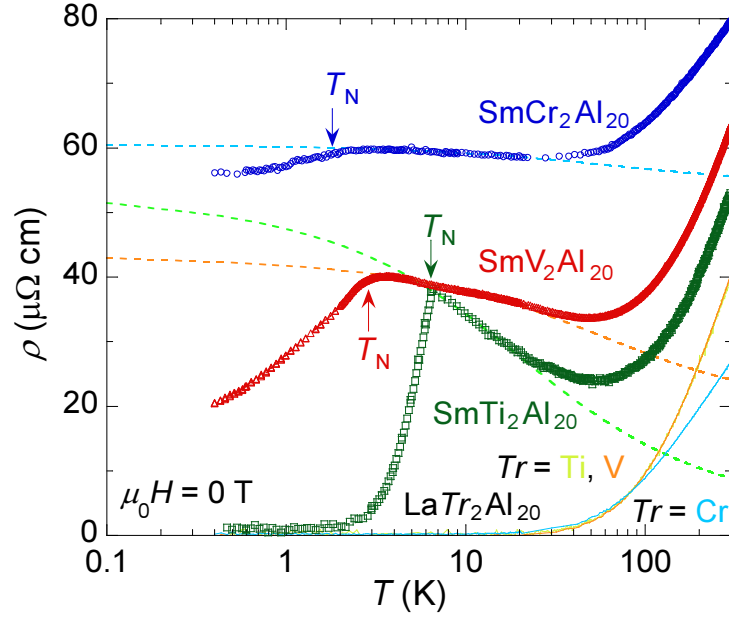


FIG. 3. (Color online) Temperature dependence of the electrical resistivity ρ of $\text{SmTr}_2\text{Al}_{20}$ ($Tr = \text{Ti}, \text{V}, \text{Cr}$). The arrows indicate the transition temperatures defined at the peak temperature of the specific heat. The dashed lines indicate the fitted curve using Hamann's expression³⁰ (see text). The solid lines indicate the inelastic component of the resistivity $\rho(T) - \rho_0$ of $\text{LaTr}_2\text{Al}_{20}$ with a residual resistivity $\rho_0 = 0.5$ ($\mu\Omega\text{cm}$) (Ti), 11.6 ($\mu\Omega\text{cm}$) (V), and 51 ($\mu\Omega\text{cm}$) (Cr).

$\chi(T)$ (open symbols). In each system, the $T_N(H)$ boundary line is almost vertical to the temperature axis, reflecting the field insensitivity of the transition temperature.

Now let us discuss the chemical trend in the valence fluctuations. According to Hamann's expression on the resistivity³⁰, the smaller slope in the logarithmic dependence of $\rho(T)$ indicates a larger Kondo temperature T_K . In fact, $\rho(T)$ in Fig. 3 can be fit to the expression (dashed lines) with $T_K \sim 20 \pm 5$ K ($Tr = \text{Ti}$), 55 ± 5 K (V), and 61 ± 20 K (Cr) for $S = 1/2$. Although the absolute value may not be correct because the model does not take into account the quartet CEF ground state, the result at least captures the correct trend, namely, the strongest Kondo effect in the Cr and the weakest in the Ti compound. Generally, the Kondo effect suppresses the entropy release due to a magnetic transition. In fact, the entropy S_{4f} reaches ~ 70 % ($Tr = \text{Ti}$), 45 % (V) and 35 % (Cr) of $R \ln 4$ at T_N (Fig. 1(b)). Besides, $\text{SmCr}_2\text{Al}_{20}$ has the largest χ at 300 K, while $\text{SmTi}_2\text{Al}_{20}$ has the smallest. All these confirm that $\text{SmCr}_2\text{Al}_{20}$ has the strongest valence fluctuations, and $\text{SmTi}_2\text{Al}_{20}$ has the weakest.

This systematic increase in the Kondo temperature and valence fluctuation scale suggests the corresponding enhancement in the c - f hybridization in order from $Tr = \text{Ti}$ to Cr. The replacement of Ti by V and Cr compresses the unit-cell volume by ~ 3 and 5 % respectively. For Sm based intermetallics, the (chemical) pressure normally decreases the Kondo temperature and increases the magnetic ordering temperature^{32,33}. Therefore, additional one (two) 3d electron(s) of Cr(V) in comparison with Ti likely play an important role in enhancing the c - f hybridization and inducing the valence fluctuations.

Furthermore, the strong valence fluctuations may be the origin for the field insensitivity of the large Sommerfeld coefficient γ and the magnetic phase boundary. The g factor for Sm compounds is small and thus significantly reduces the Zeeman energy scale of the CEF ground state in comparison with, for instance, Ce compounds³⁴. However, the smallness of the g factor alone cannot explain the robust feature against such a large field as 9 T. Instead, the nonmagnetic Sm^{2+} state stabilized by the valence fluctuations might play an important role in making the ground state robust against the magnetic field.

A similar type of the remarkably stable heavy fermion state has been discovered in $\text{SmOs}_4\text{Sb}_{12}$ ¹⁰ and has attracted much attention. To explain such a magnetically robust heavy fermion state, the rattling of the f -electron has been inferred as a plausible mechanism¹⁶⁻¹⁹. However, in our systems, the rattling mechanism is unlikely because no particularly large thermal displacement factor has been found for the Sm ion among the series of $R\text{Tr}_2\text{Al}_{20}$ ³⁵.

The fact that the increase in the Kondo coupling and valence fluctuation in turn decreases the ordering temperature suggests a proximity to a quantum critical point. We would note that, to the best of our knowledge, there has been no systematic study on quantum criticality in mixed valent Sm compounds. If T_N is much suppressed, anomalous metallic

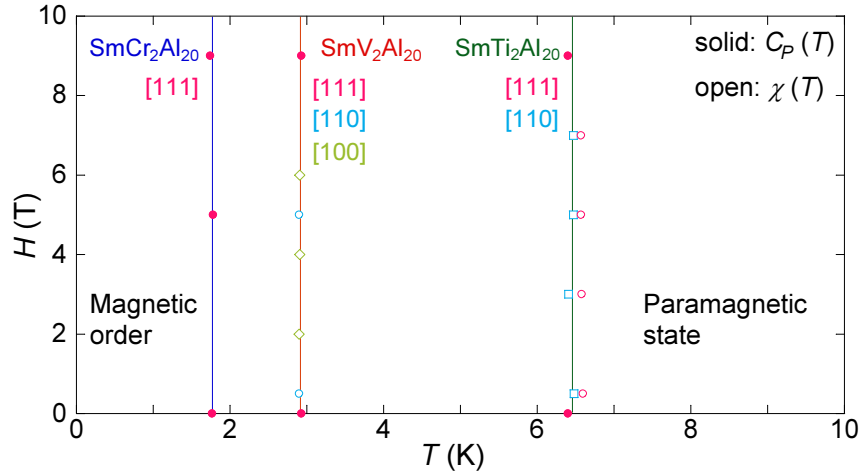


FIG. 4. (Color online) T - H phase diagram of $\text{SmTr}_2\text{Al}_{20}$ ($\text{Tr} = \text{Ti}, \text{V}, \text{Cr}$) constructed by measurements made under fields along [100] (diamond), [110] (square) and [111] (circle). The open symbols are determined from the cusp of $\chi(T)$ and solid symbols are determined from the peak of $C_P(T)$. The solid lines are guides to the eye.

behavior and superconductivity might emerge in these systems. Further investigation is necessary to elucidate such possibilities.

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